ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE2588
Silicon NPN Transistor
Horizontal Output for HDTV

Features:

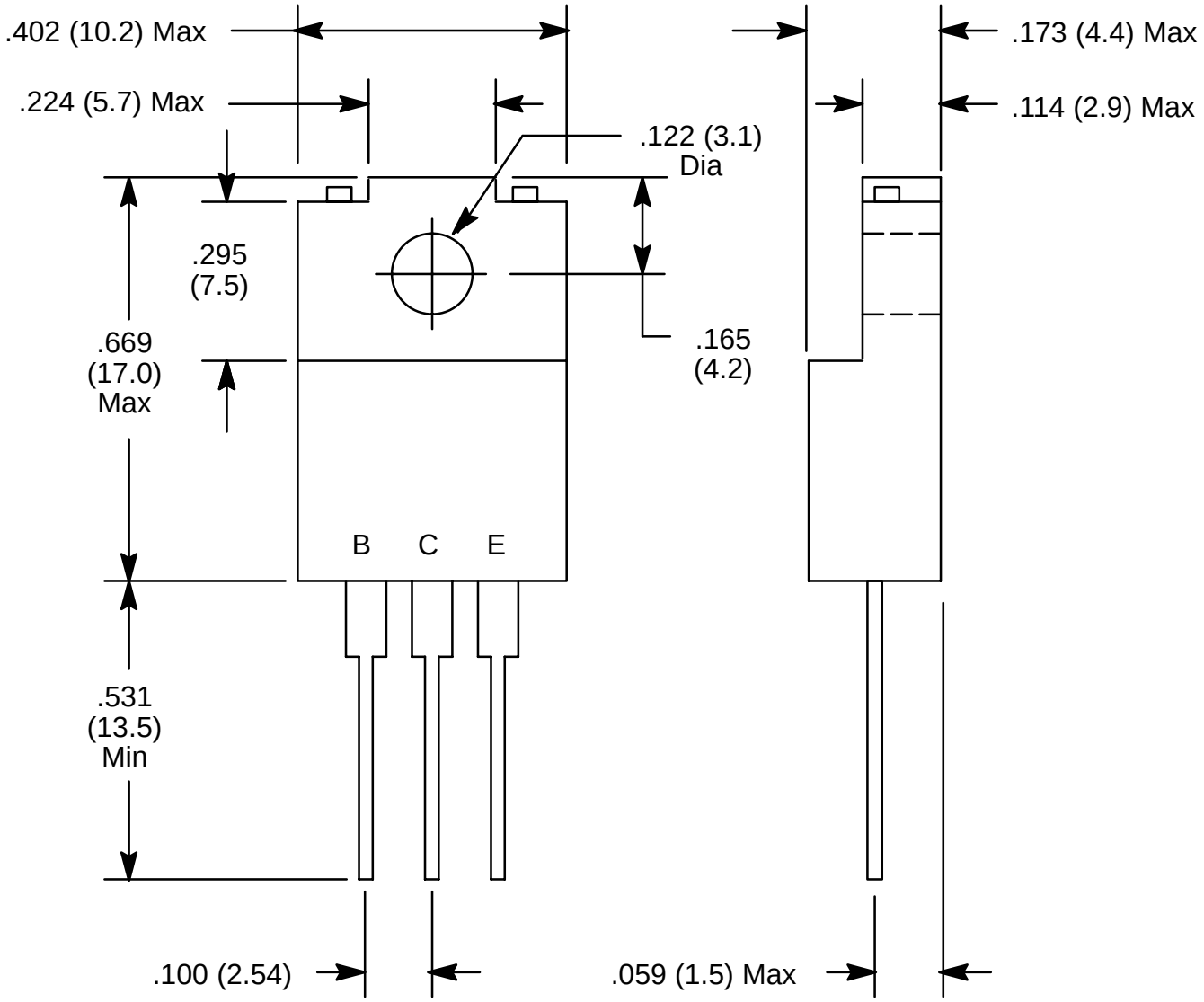
- High Breakdown Voltage: $V_{(BR)CEO}$ = 1200V Min
- Isolated TO220 Type Package

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 1500V
Collector–Emitter Voltage, V_{CEO} 1200V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C
Continuous 30mA
Peak 100mA
Collector Power Dissipation, P_C 2W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C
Maximum Thermal Resistance, Junction–to–Case, R_{thJC} . . . . . 8.3°C/W

Electrical Characteristics: (T_C = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 1200V, I_E = 0	–	–	1	µA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0	–		1	µA
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 1.5A	10	–	60	
Gain Bandwidth Product	f_T	V_{CE} = 10V, I_C = 1.5A	–	6	–	MHz
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 3mA, I_B = 0.6mA	–	–	5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 3mA, I_B = 0.6mA	–	–	2	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 100µA, I_E = 0	1500	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, R_{BE} = ∞	1200	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 100µA, I_C = 0	5	–	–	V
Output Capacitance	C_{ob}	V_{CB} = 100V, f = 1MHz	–	2.0	–	pF



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